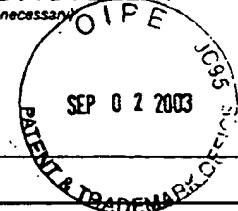


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Application Number	09/945500
Filing Date	August 30, 2001
First Named Inventor	Forbes, Leonard
Group Art Unit	2818
Examiner Name	Pham, Ly

Sheet 1 of 1

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EXAMINER

DATE CONSIDERED

12/11/03